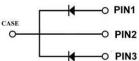


Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F (135°C)}	56A ⁽²⁾
Q _C	208nC ⁽²⁾





Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

Package: TO-247AB
 Molding compound meets UL 94 V-0 flammability rating, -, halogen-free

Terminals: Tin plated leadsPolarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112040NCTGH
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V _{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ Tc=25°C			59/118
Continuous forward current @ T _C =135°C	I _F	А	28/56
Continuous forward current @ T _C =152°C			20/40
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	Α	160 ⁽¹⁾
Power Dissipation@ T _C =25°C	Ртот	w	263/517
Power Dissipation@ T _C =110°C	Ртот		114/224
i²t Value@ Tc=25°C ,tp=10ms	∫ i²dt	A ² S	128 ⁽¹⁾
Operating junction and Storage temperature range	T_j , T_{stg}	°C	-55 to +175

⁽¹⁾ Per Leg, ⁽²⁾ Per Device



■Electrical Characteristics (Per Leg)

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	VF	V	I _F =20A, T _j =25°C	1.4	1.55
			I _F =20A, T _j =175°C	1.95	-
Reverse leakage current	I _R	μA	V _R =1200V, T _j =25°C	0.5	20
			V _R =1200V, T _j =175°C	4	-
Total capacitive charge	Qc	nC	V_R =800V, T_j =25°C, Q_C = $\int_0^{VR} C(V) dV$	104	-
Total capacitance	С	pF	V _R =0V, f=1MHZ	1509	-
			V _R =400V, f=1MHZ	98	-
			V _R =800V, f=1MHZ	70	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	27	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	R _{eJ-C}	°C W	0.57 ⁽¹⁾ 0.29 ⁽²⁾

⁽¹⁾ Per Leg, ⁽²⁾ Per Device

■Typical Characteristics (Per Leg)

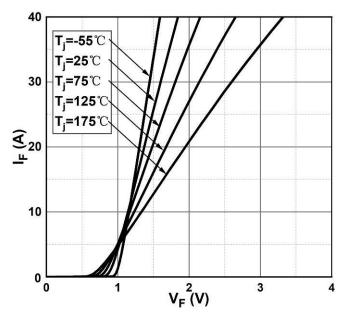


Figure 1. Forward Characteristics

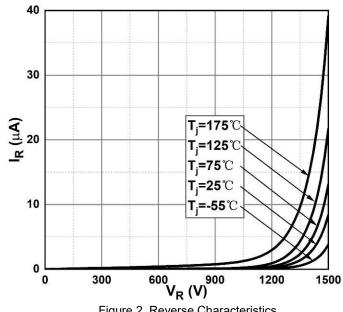
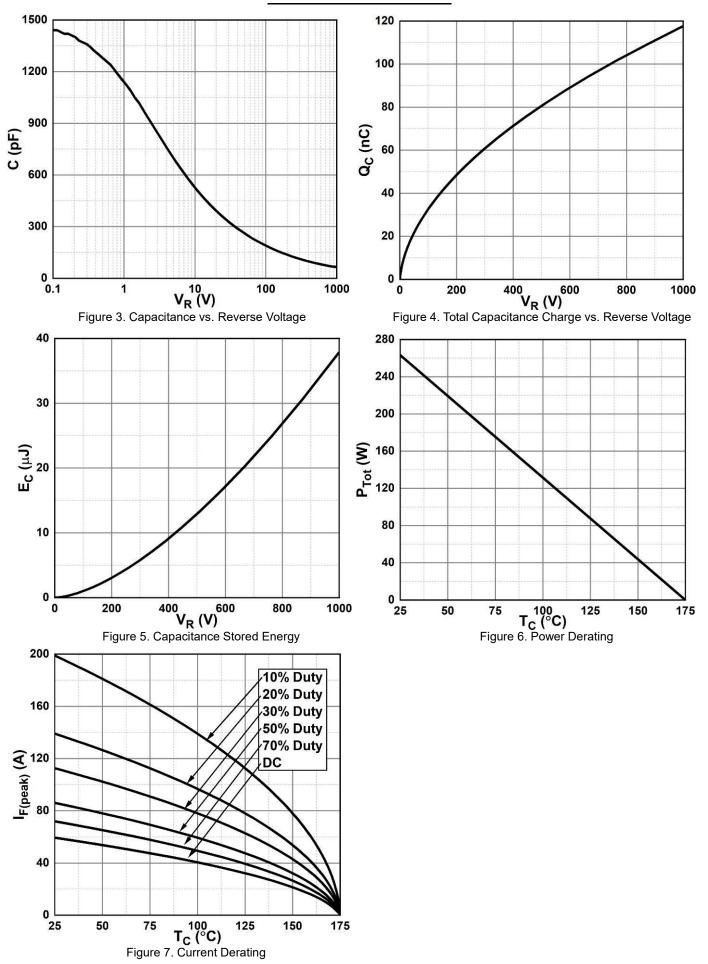


Figure 2. Reverse Characteristics





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■Typical Characteristics (Device)

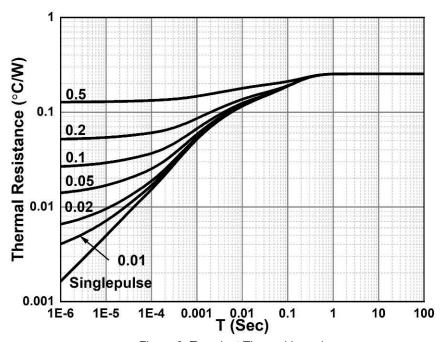
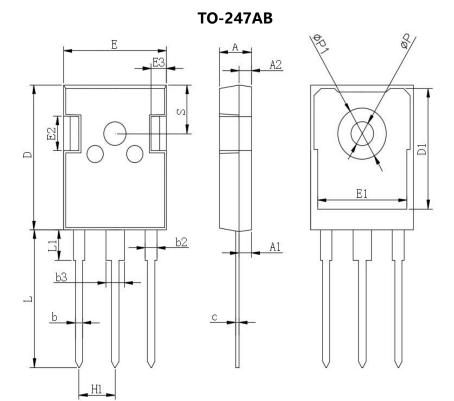


Figure 8. Transient Thermal Impedance



■Outline Dimensions



TO-247AB				
Dim	Min	Max		
Α	4.80	5.20		
A1	2.21	2.61		
A2	1.85	2.15		
b	1.0	1.4		
b2	1.91	2.21		
С	0.5	0.7		
D	20.70	21.30		
D1	16.25	16.85		
Е	15.50	16.10		
E1	13.0	13.6		
E2	4.80	5.20		
E3	2.30	2.70		
L	19.62	20.22		
L1	-	4.30		
ΦР	3.40	3.80		
ФР1	-	7.30		
S	6.15TYP			
H1	5.44TYP			
b3	2.80	3.20		



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